

# Man Young Sung

## List of Publications by Year in descending order

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57  
papers

222  
citations

1307594

7  
h-index

1125743

13  
g-index

57  
all docs

57  
docs citations

57  
times ranked

230  
citing authors

#	ARTICLE	IF	CITATIONS
1	Post-annealing processes to improve inhomogeneity of Schottky barrier height in Ti/Al 4H-SiC Schottky barrier diode. <i>Microelectronic Engineering</i> , 2016, 154, 69-73.	2.4	39
2	Effects of excess Sb on crystallization of $\gamma$ -phase SbTe binary thin films. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2008, 205, 1636-1640.	1.8	24
3	Shielding region effects on a trench gate IGBT. <i>Microelectronics Journal</i> , 2008, 39, 57-62.	2.0	17
4	A Novel Trench IGBT With a Deep $\text{P}^+$ Layer Beneath the Trench Emitter. <i>IEEE Electron Device Letters</i> , 2009, 30, 82-84.	3.9	16
5	Semiconductor nanowires surrounded by cylindrical Al <sub>2</sub> O <sub>3</sub> shells. <i>Journal of Electronic Materials</i> , 2003, 32, 1344-1348.	2.2	14
6	The effect of a shielding layer on breakdown voltage in a trench gate IGBT. , 2007, , .		14
7	67-3: Bottom-Gate ELA Poly-Si TFT for High-Resolution AMOLED Mobile Displays. <i>Digest of Technical Papers SID International Symposium</i> , 2016, 47, 923-926.	0.3	10
8	Novel Process to Improve Defect Problems for Thermal Nanoimprint Lithography. <i>IEEE Transactions on Semiconductor Manufacturing</i> , 2007, 20, 13-19.	1.7	8
9	Unbalanced Layout Method for the 4H-SiC JBS Diode Offering Improved Tradeoff between Leakage Current and ON-Resistance. <i>IEEE Electron Device Letters</i> , 2016, 37, 1045-1047.	3.9	7
10	Observation of hexagonal nuclei in the once melt-quenched Ge <sub>2</sub> Sb <sub>2</sub> Te <sub>5</sub> phase change contact dimensions. <i>Applied Physics Letters</i> , 2007, 91, 083508.	3.3	6
11	A New CMOS Read-out IC for Uncooled Microbolometer Infrared Image Sensor. <i>Journal of Infrared, Millimeter and Terahertz Waves</i> , 2008, 29, 953-965.	0.6	6
12	A new edge termination technique to improve voltage blocking capability and reliability of field limiting ring for power devices. , 2008, , .		6
13	High performance read-out IC design for IR image sensor applications. <i>Analog Integrated Circuits and Signal Processing</i> , 2010, 64, 147-152.	1.4	5
14	A CMOS Readout IC Design for Uncooled Infrared Bolometer Image Sensor Application. , 2006, , .		4
15	A New Organic Thin-Film Transistor Based Current-Driving Pixel Circuit for Active-Matrix Organic Light-Emitting Displays. , 2007, , .		4
16	Liquid Lens Module with Wide Field-of-View and Variable Focal Length. <i>Electronic Materials Letters</i> , 2010, 6, 141-144.	2.2	4
17	An Analog Front-End IC Design for 320 $\times$ 240 Microbolometer Array Applications. <i>IEEE Transactions on Circuits and Systems II: Express Briefs</i> , 2015, 62, 1048-1052.	3.0	4
18	A new lateral trench IGBT with p <sup>+</sup> diverter having superior electrical characteristics. , 0, , .		3

#	ARTICLE	IF	CITATIONS
19	A novel trench IGBT with a rectangular oxide beneath the trench gate. , 2009, , .		3
20	All digital on-chip temperature sensor using dual ring oscillators. , 2013, , .		3
21	Investigation of the layout and optical proximity correction effects to control the trench etching process on 4H-SiC. Electronic Materials Letters, 2017, 13, 368-372.	2.2	3
22	Enhancement of On-Resistance Characteristics Using Charge Balance Analysis Modulation in a Trench Filling Super Junction MOSFET. Journal of Electrical Engineering and Technology, 2014, 9, 843-847.	2.0	3
23	ESD Protection Circuit with Separated GGNMOS Segment for Input Protection. , 0, , .		2
24	A novel current driving method using organic TFT pixel circuit for active-matrix OLED. , 2007, , .		2
25	An improvement of the breakdown voltage characteristic of trench gate IGBTs by using a shielding layer. , 2007, , .		2
26	Design of field limiting ring employing trench structure for high power devices. IEICE Electronics Express, 2009, 6, 1621-1625.	0.8	2
27	Improving Current Density of 4H-SiC Junction Barrier Schottky Diode with Wide Trench Etching. Journal of Nanoscience and Nanotechnology, 2016, 16, 11686-11691.	0.9	2
28	A small sized lateral trench electrode IGBT having improved latch-up and breakdown characteristics for power IC system. , 0, , .		1
29	Bias Offset Correction Technique For Uncooled Infrared Bolometer Sensor Readout IC. , 0, , .		1
30	Deposition of LiNbO3 thin films for selective etching. Journal of Electroceramics, 2006, 17, 933-935.	2.0	1
31	Design of an organic TFT pixel electrode circuit with enhanced current programming method for active-matrix OLED displays. , 2007, , .		1
32	Use of the p-floating shielding layer for improving electric field concentration of the recessed gate. , 2008, , .		1
33	A pre-emphasis output buffer control scheme for a GDDR3 SDRAM interface. IEICE Electronics Express, 2008, 5, 446-450.	0.8	1
34	Metal-ferroelectric-metal capacitor based persistent memory for electronic product code class-1 generation-2 uhf passive radio-frequency identification tag. Journal of Applied Physics, 2009, 105, 061628.	2.5	1
35	FLOATING-BASE BJT TYPE ESD DEVICE FOR RFID CHIP. Integrated Ferroelectrics, 2009, 105, 45-52.	0.7	1
36	Dual Field Communication Scheme for UHF (860-960 MHz) Gen2 RFID Chip. Integrated Ferroelectrics, 2011, 125, 1-10.	0.7	1

#	ARTICLE	IF	CITATIONS
37	A novel lateral trench IGBT employing the p+ diverter having superior forward blocking and latch-up characteristics. , 0, , .		0
38	Simulation of a lateral trench IGBT with p+ diverter having superior electrical characteristics. , 0, , .		0
39	Dual-channel SOI LIGBT with improved latch-up and forward voltage drop characteristics. , 0, , .		0
40	Effect of Excimer Laser Annealing on Optical Properties of GaN Films Deposited by R.F. Magnetron Sputtering. Materials Research Society Symposia Proceedings, 2001, 693, 507.	0.1	0
41	Lateral trench IGBT with effective p/sup +/ diverter having superior electrical characteristics for smart power IC. , 0, , .		0
42	Electrical characteristics of a new lateral trench electrode IGBT for smart power IC. , 0, , .		0
43	Simulation of a lateral trench IGBT with p/sup +/ diverter for improving latch-up characteristics. , 0, , .		0
44	A novel trench-type LIGBT having superior electrical characteristics. , 0, , .		0
45	The Fabrication and Experimental Results of a New Lateral Trench Electrode IGBT with a p+ Diverter. Journal of Computational Electronics, 2003, 2, 21-28.	2.5	0
46	A new EST with dual trench gate electrode (DTG-EST). , 0, , .		0
47	Photocurrent in a hybrid system of 1-thioglycerol and HgTe quantum dots. Materials Research Society Symposia Proceedings, 2003, 789, 115.	0.1	0
48	The characteristics of joints with Indium-silver alloy using diffusion soldering method. Materials Research Society Symposia Proceedings, 2004, 817, 13.	0.1	0
49	Design of readout IC for uncooled infrared bolometer sensor using bias offset correction technique. , 2005, , .		0
50	ESD protection circuit with an improved ESD capability for input or output circuit protection. , 2005, , .		0
51	Effects of Channel Doping Profile on Electrical Characteristics of Impact Ionization MOS. , 0, , .		0
52	A DUAL-GATE CELL (DGC) FeRAM WITH NDRO AND RANDOM ACCESS SCHEME FOR NANOSCALE AND TERABIT NON-VOLATILE MEMORY. Integrated Ferroelectrics, 2006, 81, 141-148.	0.7	0
53	Current Insertion Transient Response for Measuring Phase Margin in Negative Feedback System. , 2007, , .		0
54	Influences of partial melting and overheating on amorphization of Ge<sub>2</sub>Sb<sub>2</sub>Te<sub>5</sub> during the reset process. Physica Status Solidi (A) Applications and Materials Science, 2008, 205, 2657-2661.	1.8	0

#	ARTICLE	IF	CITATIONS
55	CRYPTO BASED EPC C1G2 UHF (860 MHzâ€“960 MHz) PASSIVE RFID TAG CHIP. Integrated Ferroelectrics, 2008, 100, 216-227.	0.7	0
56	On-chip stacked punchthrough diode design for 900V power MOSFET gate ESD protection. , 2014, , .		0
57	A Novel Trench IGBT With a Deep $\text{P}^+$ Layer Beneath the Trench Emitter. IEEE Electron Device Letters, 2009, , .	3.9	0